

Low Distortion Internally Matched Power GaAs FETs (C-Band)

Features

- Low intermodulation distortion
 - $IM_3 = -45$ dBc at $P_o = 31.5$ dBm,
 - Single carrier level
- High power
 - $P_{1dB} = 42.5$ dBm at 5.9 GHz to 6.4 GHz
- High gain
 - $G_{1dB} = 8.0$ dB at 5.9 GHz to 6.4 GHz
- Broad band internally matched
- Hermetically sealed package

RF Performance Specifications ($T_a = 25^\circ C$)

Characteristics	Symbol	Condition	Unit	Min.	Typ.	Max
Output Power at 1dB Compression Point	P_{1dB}	$V_{DS} = 10V$ $f = 5.9 \sim 6.4$ GHz	dBm	42.0	42.5	-
Power Gain at 1dB Compression Point	G_{1dB}		dB	7.0	8.0	-
Drain Current	I_{DS1}		A	-	4.8	5.5
Gain Flatness	ΔG		dB	-	-	± 0.8
Power Added Efficiency	η_{add}	Note 1	%	-	31	-
3rd Order Intermodulation Distortion	IM_3		dBc	-42	-45	-
Drain Current	I_{DS2}		A	-	4.8	5.5
Channel-Temperature Rise	ΔT_{ch}	$V_{DS} \times I_{DS} \times R_{th}(c-c)$	°C	-	-	80

Electrical Characteristics ($T_a = 25^\circ C$)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max
Trans-conductance	gm	$V_{DS} = 3V$ $I_{DS} = 6.0A$	mS	-	3600	-
Pinch-off Voltage	V_{GSoff}	$V_{DS} = 3V$ $I_{DS} = 80mA$	V	-2.0	-3.5	-5.0
Saturated Drain Current	I_{DSS}	$V_{DS} = 3V$ $V_{GS} = 0V$	A	-	11.6	15.0
Gate-Source Breakdown Voltage	V_{GSO}	$I_{GS} = -240\mu A$	V	-5	-	-
Thermal Resistance	R_{th} (c-c)	Channel to Case	°C/W	-	1.4	1.8

Note 1: 2 tone Test $P_{out} = 31.5$ dBm Single Carrier Level.

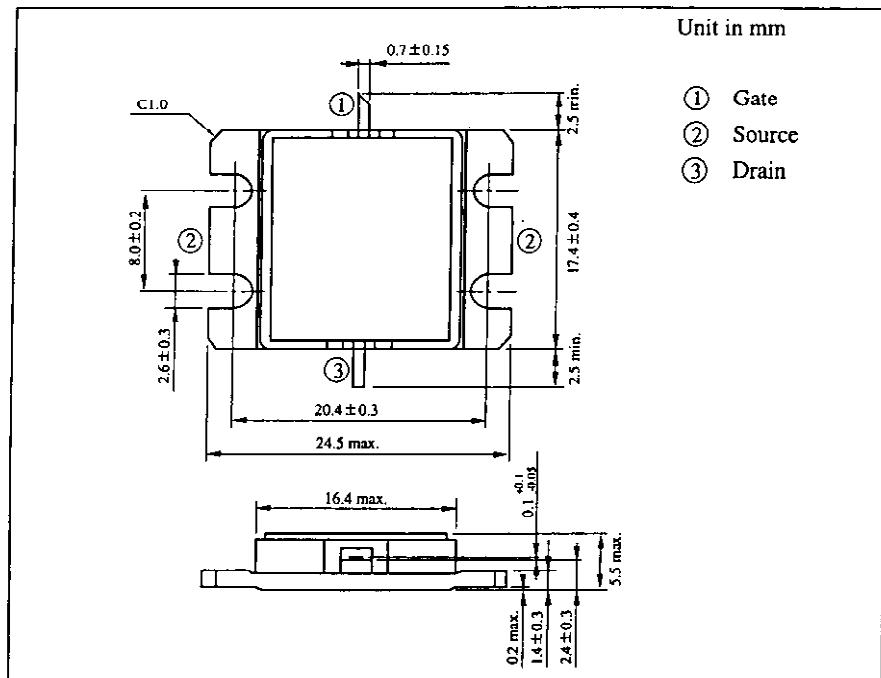
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Absolute Maximum Ratings (Ta = 25° C)

Characteristic	Symbol	Unit	Rating
Drain-Source Voltage	V _{DS}	V	15
Gate-Source Voltage	V _{GS}	V	-5
Drain Current	I _{DS}	A	16
Total Power Dissipation (T _c = 25°C)	P _T	W	70
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65~175

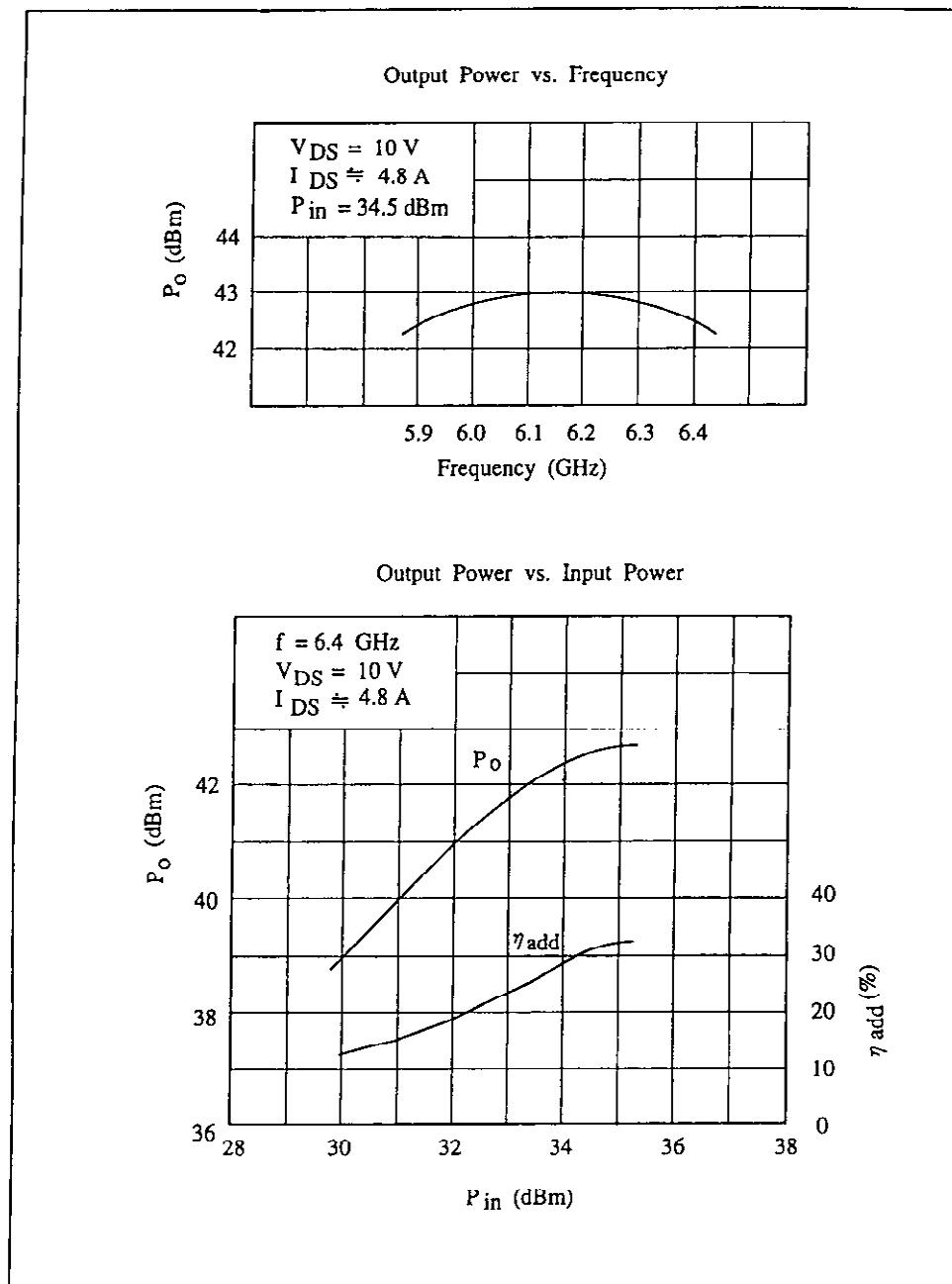
Package Outline (2-16G1B)



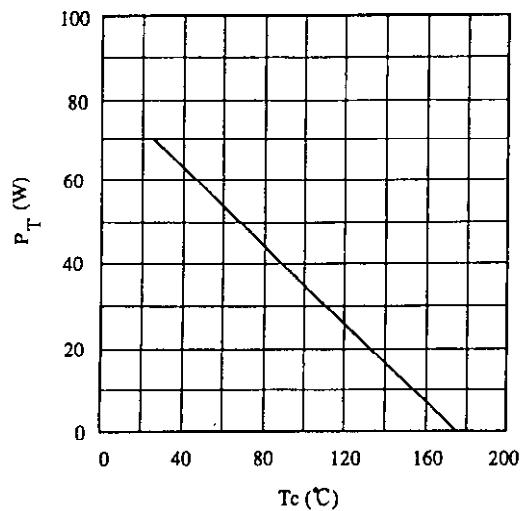
Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF Performances



Power Dissipation vs. Case Temperature

IM₃ vs. Output Power Characteristics